



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

SURFACE MOUNT
NPN Digital Silicon Transistor

VOLTAGE 50 Volts CURRENT 30 mAmpere

CHUMH1GP

APPLICATION

* Switching circuit, Inverter, Interface circuit, Driver circuit.

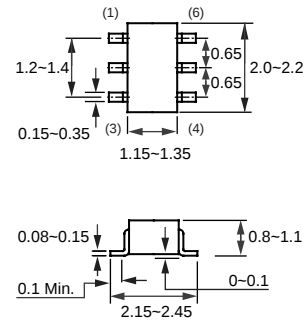
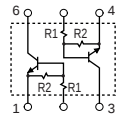
FEATURE

- * Small surface mounting type. (SC-88/SOT-363)
- * High current gain.
- * Suitable for high packing density.
- * Low collector-emitter saturation.
- * High saturation current capability.
- * two CHDTC124E chips in one package.
- * Built in bias resistor(R1=22k Ω , Typ.)



SC-88/SOT-363

CIRCUIT



Dimensions in millimeters

SC-88/SOT-363

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	Supply voltage		—	50	V
V _{IN}	Input voltage		-10	+40	V
I _O	DC Output current		—	30	mA
P _{TOT}	Total power dissipation	T _{amb} ≤ 25 °C, Note 1	—	150	mW
T _{STG}	Storage temperature		-55	+150	°C
T _J	Junction temperature		—	150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC (CHUMH1GP)

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{I(off)}	Input off voltage	I _o =100uA; V _{cc} =5.0V	0.5	–	–	V
V _{I(on)}	Input on voltage	I _o =5mA; V _o =0.2V	–	–	3.0	V
V _{O(on)}	Output voltage	I _o =10mA; I _i =0.5mA	–	0.1	0.3	V
I _i	Input current	V _i =5V	–	–	0.36	mA
I _{C(off)}	Output current	V _i =0V; V _{cc} =50V	–	–	0.5	uA
h _{FE}	DC current gain	I _o =5mA; V _o =5.0V	56	–	–	
R ₁	Input resistor		15.4	22	28.6	KΩ
R ₂ /R ₁	Resistor ratio		0.8	1.0	1.2	

Note

1.Pulse test: t_p≤300uS; δ≤0.02.

RATING CHARACTERISTIC CURVES (CHUMH1GP)

Typical Electrical Characteristics

Fig.1 Input voltage vs. output current
(ON characteristics)

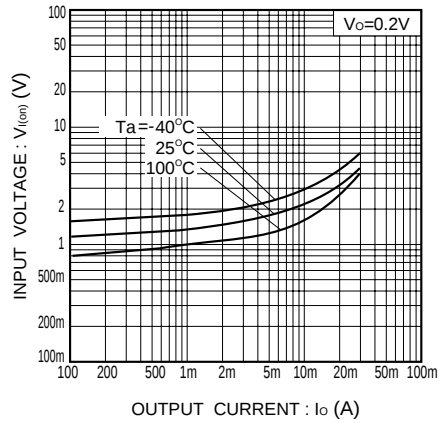


Fig.2 Output current vs. input voltage
(OFF characteristics)

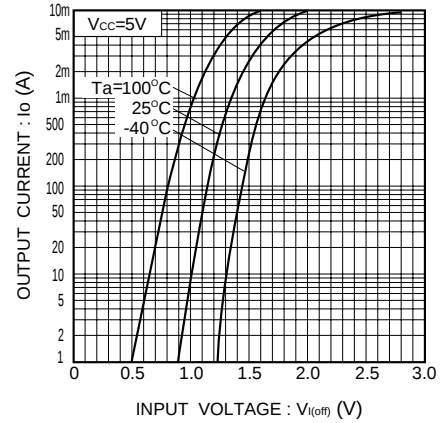


Fig.3 DC current gain vs. output current

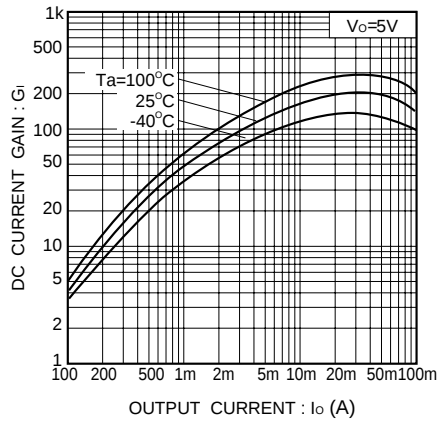


Fig.4 Output voltage vs. output current

